

Bias Resistor Transistor

PNP Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

- **Applications**
Inverter, Interface, Driver
- **Features**

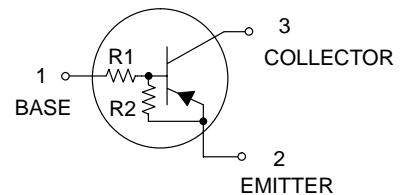
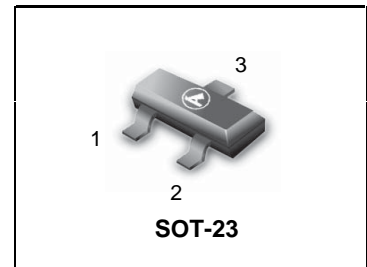
- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on / off conditions need to be set for operation, making the device design easy.

- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

• **Absolute maximum ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	V _{CC}	-50	V
Input voltage	V _{IN}	-40 to +10	V
Output current	I _C	-500	mA
Power dissipation	P _D	200	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

LDTB114ELT1G
S-LDTB114ELT1G



DEVICE MARKING AND RESISTOR VALUES

Device	Marking	R1 (K)	R2 (K)	Shipping
LDTB114ELT1G S-LDTB114ELT1G	F14	10	10	3000/Tape & Reel
LDTB114ELT3G S-LDTB114ELT3G	F14	10	10	10000/Tape & Reel

• **Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V _{I(off)}	-	-	-0.5	V	V _{CC} =-5V, I _O =-100μA
	V _{I(on)}	-3	-	-		V _O =-0.3V, I _O =-10mA
Output voltage	V _{O(on)}	-	-0.1	-0.3	V	I _O /I _I =-50mA/-2.5mA
Input current	I _I	-	-	-0.88	mA	V _I =-5V
Output current	I _{O(off)}	-	-	-0.5	μA	V _{CC} =-50V, V _I =0V
DC current gain	G _I	56	-	-	-	V _O =-5V, I _O =-50mA
Input resistance	R ₁	7	10	13	kΩ	-
Resistance ratio	R ₂ /R ₁	0.8	1	1.2	-	-
Transition frequency	f _T *	-	200	-	MHz	V _{CE} =-10V, I _E =50mA, f=100MHz

* Characteristics of built-in transistor

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●Electrical characteristic curves

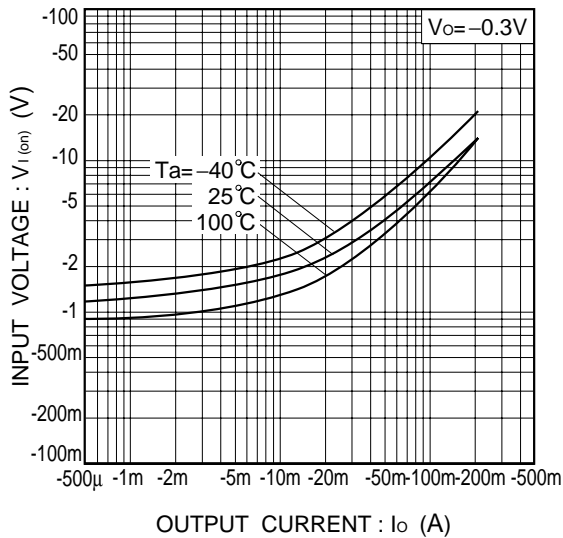


Fig.1 Input voltage vs. output current (ON characteristics)

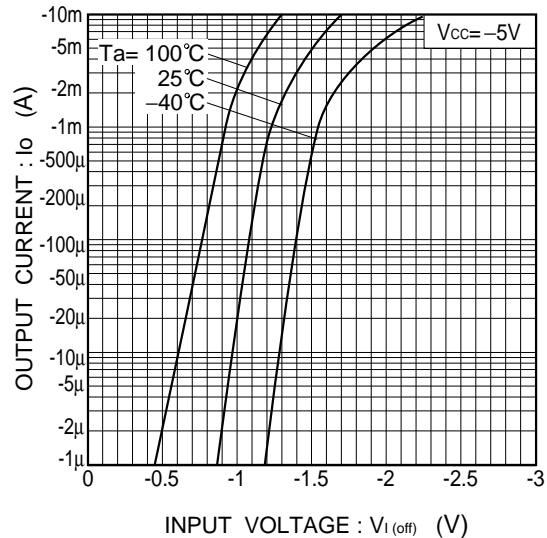


Fig.2 Output current vs. input voltage (OFF characteristics)

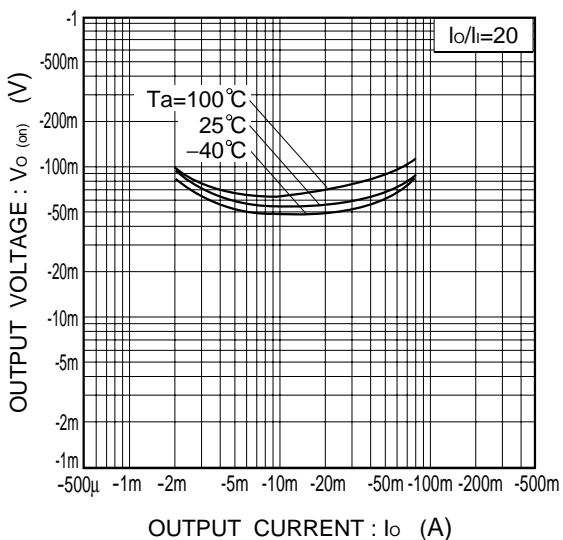


Fig.4 Output voltage vs. output current

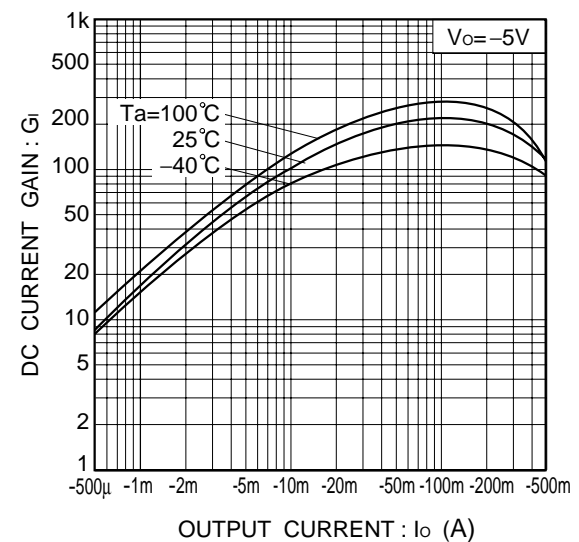


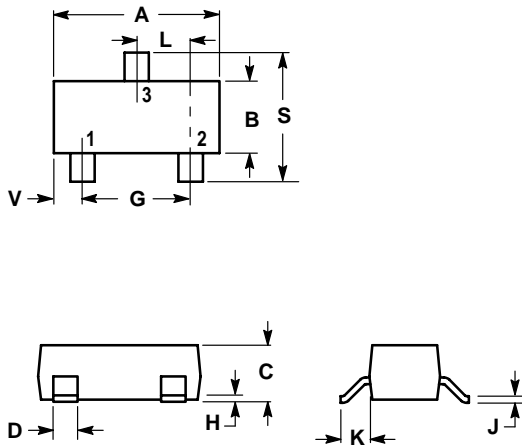
Fig.3 DC current gain vs. output current

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60



单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)